

S. N. 10/050,169
Preliminary Amendment

REMARKS

The amendments to claims 1, 2, and 18 are made to more clearly define the invention.

In view of the aforementioned amendments and remarks, claims 1, 2 and 18, as amended, and newly added claims 24 to 37 are believed to be in condition for allowance, which action is requested.

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned "**Version with markings to show changes made.**"

In the event that this paper is not timely filed, Applicants respectfully petition for an appropriate extension of time. The fees for such an extension or any other fees which may be due with respect to this paper, may be charged to Deposit Account No. 01-2340.

Respectfully submitted,

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Enclosure: Version with markings to show changes made
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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend Claim 1, as follows:

1. (Amended) A semiconductor device comprising:
 - a semiconductor substrate;
 - a first insulating film formed over said semiconductor substrate;
 - a capacitor formed over said first insulating film, and having one electrode which includes an extension extending over said first insulating film;
 - a second insulating film formed over said first insulating film;
 - a first contact hole formed through said second insulating film and said extension of the one electrode; and
 - a first conductor pattern burying said first contact hole.

Please amend Claim 2, as follows:

2. (Amended) A semiconductor device comprising:
 - a semiconductor substrate;
 - a first insulating film formed over said semiconductor substrate;
 - a first conducting plug formed in said first insulating film;
 - a storage electrode formed over said first insulating film, and electrically connected to said conducting plug;

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a capacitor dielectric film formed over said storage electrode;
an opposing electrode formed over said capacitor dielectric film, and having an extension extending over said first insulating film;
a second insulating film formed over said opposing electrode;
a first contact hole formed through said second insulating film and said extension of the opposing electrode; and
a first conductor pattern burying said contact hole.

Please amend Claim 18, as follows:

18. (Amended) The semiconductor memory device according to claim 17, wherein said bit line includes a conducting bit layer, oxide side walls on side walls of the conducting bit layer, and a bit silicon nitride layer covering the conducting bit layer and the oxide side walls of the bit line [bit silicon nitride layer].